MOSFETs Silicon N-channel MOS (U-MOSⅧ-H)

TPH1R403NL

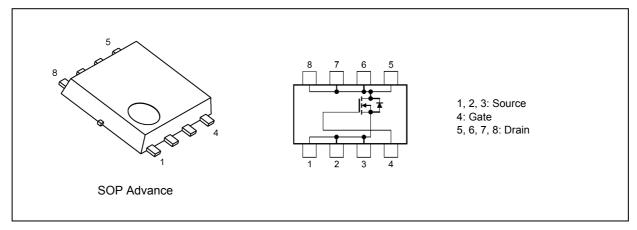
1. Applications

- High-Efficiency DC-DC Converters
- Switching Voltage Regulators

2. Features

- (1) High-speed switching
- (2) Small gate charge: $Q_{SW} = 10.6 \text{ nC}$ (typ.)
- (3) Low drain-source on-resistance: $R_{DS(ON)}$ = 1.7 mO (typ.) (V_{GS} = 4.5 V)
- (4) Low leakage current: I_{DSS} = 10 μA (max) (V_{DS} = 30 V)
- (5) Enhancement mode: V_{th} = 1.3 to 2.3 V (V_{DS} = 10 V, I_{D} = 0.5 mA)

3. Packaging and Internal Circuit



4. Absolute Maximum Ratings (Note) (T_a = 25 °C unless otherwise specified)

Characteris	Symbol	Rating	Unit		
Drain-source voltage			V _{DSS}	30	V
Gate-source voltage			V _{GSS}	±20	1
Drain current (DC)	(Silicon limit)	(Note 1), (Note 2)	I _D	150	A
Drain current (DC)	(T _c = 25 °C)	(Note 1)	I _D	60	1
Drain current (pulsed)	(t = 1 ms)	(Note 1)	I _{DP}	200	1
Power dissipation	(T _c = 25 °C)		PD	64	W
Power dissipation	(t = 10 s)	(Note 3)	PD	2.8	1
Power dissipation	(t = 10 s)	(Note 4)	PD	1.6	1
Single-pulse avalanche energy		(Note 5)	E _{AS}	355	mJ
Avalanche current			I _{AR}	60	A
Channel temperature			T _{ch}	150	°C
Storage temperature			T _{stg}	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Start of commercial production

5. Thermal Characteristics

Characteristics	Symbol	Max	Unit		
Channel-to-case thermal resistance	(T _c = 25 °C)		R _{th(ch-c)}	1.95	°C/W
Channel-to-ambient thermal resistance	(t = 10 s)	(Note 3)	R _{th(ch-a)}	44.6	
Channel-to-ambient thermal resistance	(t = 10 s)	(Note 4)	R _{th(ch-a)}	78.1	

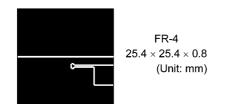
Note 1: Ensure that the channel temperature does not exceed 150 °C.

Note 2: Limited by silicon chip capability. Package limit is 60 A.

Note 3: Device mounted on a glass-epoxy board (a), Figure 5.1

Note 4: Device mounted on a glass-epoxy board (b), Figure 5.2

Note 5: V_{DD} = 24 V, T_{ch} = 25 °C (initial), L = 76 μ H, I_{AR} = 60 A



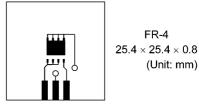


Fig. 5.1 Device Mounted on a Glass-Epoxy Board (a) Fig. 5.2 Device Mounted on a Glass-Epoxy Board (b)

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

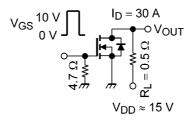
6. Electrical Characteristics

6.1. Static Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I _{GSS}	V_{GS} = ±20 V, V_{DS} = 0 V	_		±0.1	μA
Drain cut-off current	I _{DSS}	V _{DS} = 30 V, V _{GS} = 0 V	_		10	
Drain-source breakdown voltage	V _{(BR)DSS}	I _D = 10 mA, V _{GS} = 0 V	30		_	V
	V _{(BR)DSX}	I _D = 10 mA, V _{GS} = -20 V	15		_	
Gate threshold voltage	V _{th}	V _{DS} = 10 V, I _D = 0.5 mA	1.3		2.3	
Drain-source on-resistance	R _{DS(ON)}	V _{GS} = 4.5 V, I _D = 30 A	_	1.7	2.1	mΩ
		V _{GS} = 10 V, I _D = 30 A	_	1.2	1.4	

6.2. Dynamic Characteristics ($T_a = 25$ °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C _{iss}	V _{DS} = 15 V, V _{GS} = 0 V, f = 1 MHz	_	3400	4400	pF
Reverse transfer capacitance	C _{rss}		_	93	200	
Output capacitance	C _{oss}]	_	1800	_	
Gate resistance	r _g	—	_	1.1	1.7	Ω
Switching time (rise time)	tr	See Fig. 6.2.1	_	5.6	_	ns
Switching time (turn-on time)	t _{on}]	_	16	_	
Switching time (fall time)	t _f]	—	8.9	_	
Switching time (turn-off time)	t _{off}]	_	50	_	



Duty \leq 1%, t_W = 10 μs

Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics ($T_a = 25$ °C unless otherwise specified)

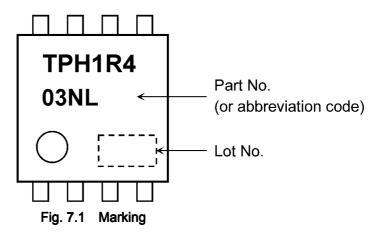
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus	Qg	$V_{DD} \approx 15 \text{ V}, \text{ V}_{GS} = 10 \text{ V}, \text{ I}_{D} = 60 \text{ A}$	_	46	_	nC
gate-drain)		$V_{DD} \approx 15 \text{ V}, \text{ V}_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 60 \text{ A}$	_	20	_	
Gate-source charge 1	Q _{gs1}	$V_{DD} \approx 15 \text{ V}, \text{ V}_{GS} = 10 \text{ V}, \text{ I}_{D} = 60 \text{ A}$	_	12.1	_	
Gate-drain charge	Q _{gd}		_	4.3	_	
Gate switch charge	Q _{SW}		_	10.6	_	

6.4. Source-Drain Characteristics ($T_a = 25 \ ^{\circ}C$ unless otherwise specified)

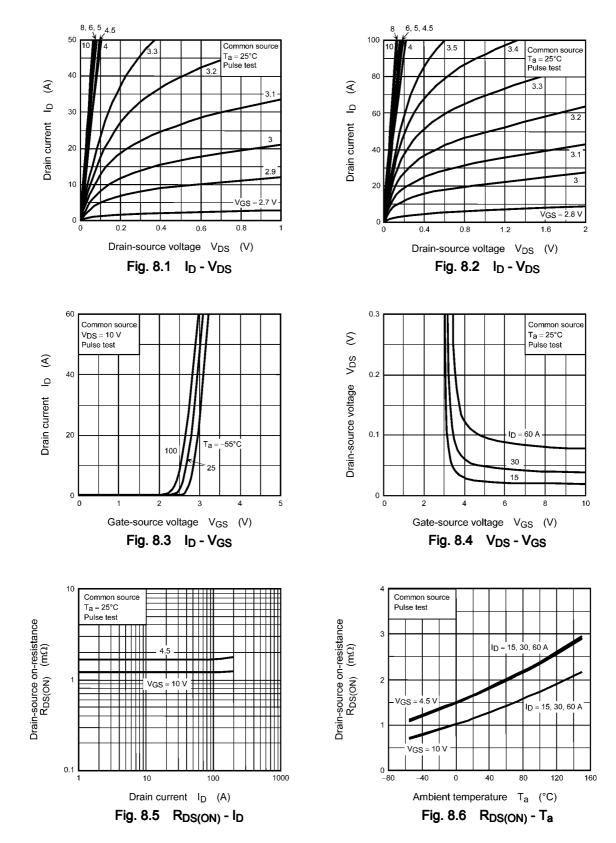
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Reverse drain current (pulsed) (Note 6) I _{DRP}	—	_	_	200	А
Diode forward voltage	V _{DSF}	I _{DR} = 60 A, V _{GS} = 0 V	_	_	-1.2	V

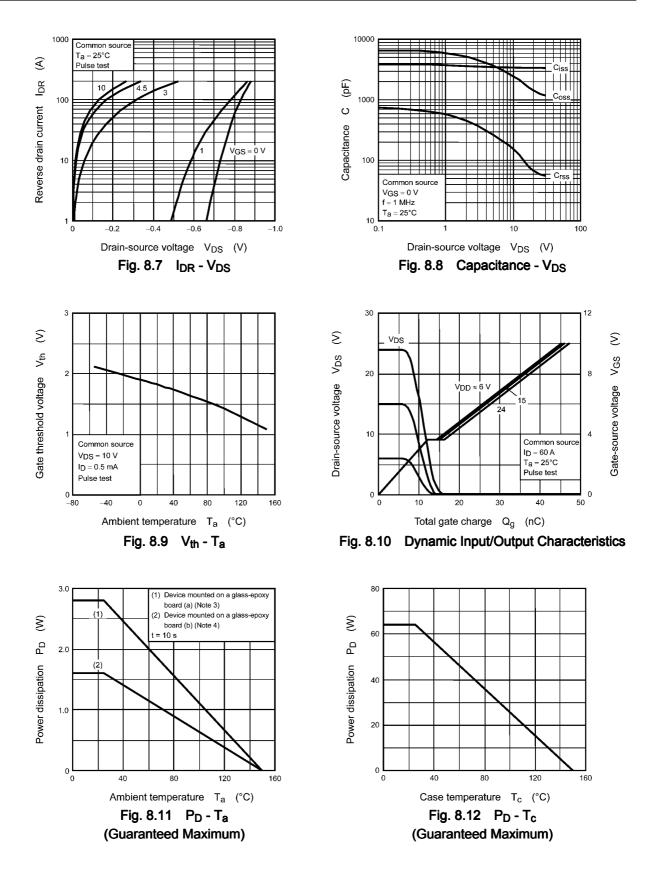
Note 6: Ensure that the channel temperature does not exceed 150 °C.

7. Marking

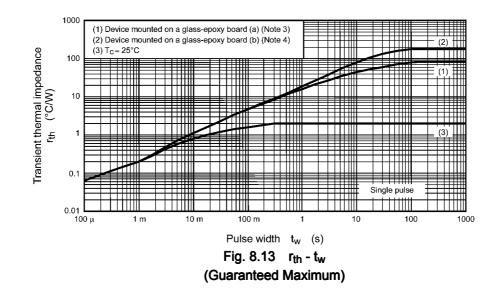


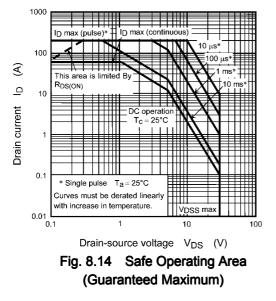
8. Characteristics Curves (Note)











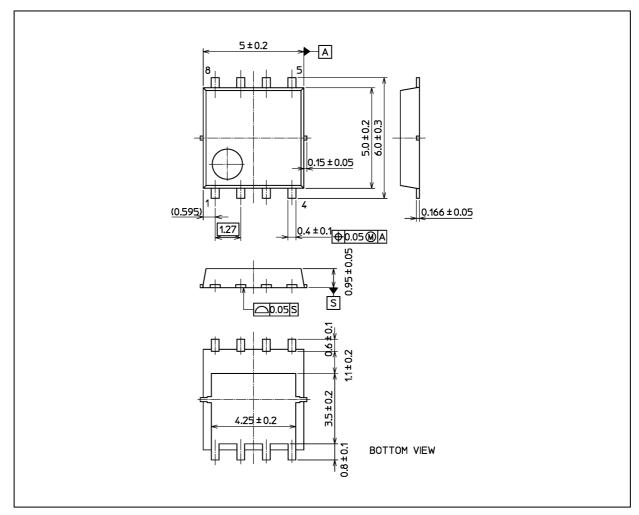
Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



TPH1R403NL

Package Dimensions

Unit: mm



Weight: 0.069 g (typ.)

TOSHIBA: 2-5Q1S

Nickname: SOP Advance

Package Name(s)

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